

Manouchehr Hosseini

List of Publications by Year in descending order

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Version: 2024-02-01

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papers

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citations

1307594

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1372567

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docs citations

11
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353
citing authors

#	ARTICLE	IF	CITATIONS
1	Strain-induced Modulation of Electron Mobility in Single-Layer Transition Metal Dichalcogenides MX_2 ($M = \text{Mo}$). <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 3192-3198.	3.0	73
2	Strain induced mobility modulation in single-layer MoS_2 . <i>Journal Physics D: Applied Physics</i> , 2015, 48, 375104.	2.8	44
3	Very large strain gauges based on single layer $MoSe_2$ and WSe_2 for sensing applications. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	32
4	A tunable hybrid graphene-metal metamaterial absorber for sensing in the THz regime. <i>Current Applied Physics</i> , 2021, 31, 132-140.	2.4	18
5	A comparative study of substrates disorder on mobility in the Graphene nanoribbon: Charged impurity, surface optical phonon, surface roughness. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2020, 116, 113763.	2.7	15
6	Electrical and electronic properties of strained mono-layer $InTe$. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2020, 118, 113875.	2.7	15
7	Field-Effect Transistor Based on $MoSi_2N_4$ and WSi_2N_4 Monolayers Under Biaxial Strain: A Computational Study of the Electronic Properties. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 863-869.	3.0	15
8	Strain effects on the DC performance of single-layer TMD-based double-gate field-effect transistors. <i>Journal of Computational Electronics</i> , 2018, 17, 1603-1607.	2.5	7
9	Investigation of layer number effects on the electrical properties of strained multi-layer MoS_2 . <i>Journal of Computational Electronics</i> , 2019, 18, 1236-1242.	2.5	5
10	Tunable electromagnetic interference shield using periodic graphene-based structures in the terahertz regime. , 2017, , .		4
11	Investigation of Double-Gate Ferroelectric FET Based on Single-Layer MoS_2 with Consideration of Contact Resistance. <i>Journal of Electronic Materials</i> , 2020, 49, 4085-4090.	2.2	3